

n-channel JFETs designed for . . .



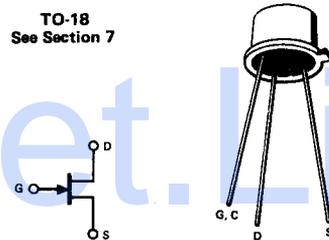
Performance Curves NP
See Section 5

■ Small-Signal Low Power Applications

***ABSOLUTE MAXIMUM RATINGS (25°C)**

Gate-Drain or Gate-Source Voltage (Note 1) -40 V
Gate Current 10 mA
Total Device Dissipation at (or below) 25°C	
Free-Air Temperature (Note 2) 300 mW
Storage Temperature Range -65 to +175°C
Maximum Operating Temperature 150°C

TO-18
See Section 7



***ELECTRICAL CHARACTERISTICS (25°C unless otherwise noted)**

Characteristic	2N3368		2N3369		2N3370		Unit	Test Conditions				
	Min	Max	Min	Max	Min	Max						
1 2 3 4 5 6	IGSS	Gate Reverse Current		-5		-5		-5	VGS = -30 V, VDS = 0	100°C		
				-1.5		-1.5		-1.5			µA	
3 4	BVGSS	Gate-Source Breakdown Voltage	-40		-40		-40	V	IG = -1 µA, VDS = 0			
				-11.5		-6.5			-3.2	VDS = 20 V, ID = 1 µA		
4 5	VGS(off)	Gate-Source Cutoff Voltage		-11.5		-6.5		-3.2	VDS = 20 V, ID = 1 µA			
				5		5		5	nA	VDS = 20 V, VGS = ()		
5 6	ID(off)	Drain Cutoff Current		5		5		5	(V)	VDS = 20 V, VGS = ()		
				(-12.0)		(-7.0)		(-3.5)		nA		
6 7	IDSS	Saturation Drain Current	2.0	12.0	0.5	2.5	0.1	0.6	mA	VDS = 30 V (Note 3), VGS = 0		
7 8 9 10	gfs	Common-Source Forward Transconductance	1000	4000	600	2500	300	2500	µmho	VDS = 30 V (Note 3), VGS = 0		f = 1 kHz
8 9	goss	Common-Source Output Conductance		80		30		15	pF	VDS = 30 V, VGS = 0		f = 1 MHz
9 10	Coss	Common-Source Output Capacitance		3		3		3	pF	VDS = 30 V, VGS = 0		f = 1 MHz
10	Ciss	Common-Source Input Capacitance		20		20		20	pF	VDS = 8 V, VGS = 0		f = 1 MHz

*JEDEC registered data.

NP

NOTES:

- Due to symmetrical geometry, these units may be operated with source and drain leads interchanged.
- Derate linearly to 150°C free-air temperature at rate of 2.1 mW/°C.
- To minimize heating on high IDSS units, this parameter is measured during a 2 ms interval 100 ms after power is applied. (Not a JEDEC condition.)